

Silicon Planar PNP Thyristor

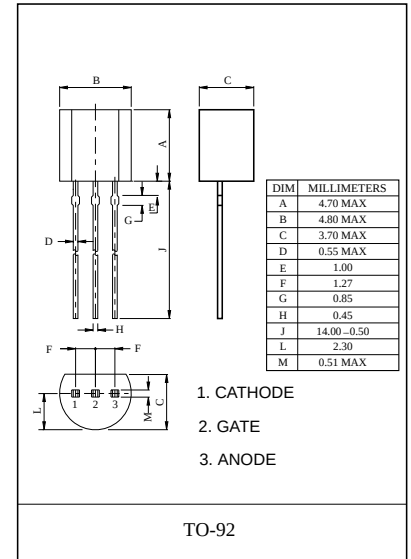
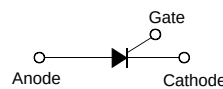
MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	MCR100-6/F	V
	MCR100-8/F	
T_J	Junction Temperature	-40 to 125 °C
T_{stg}	Storage Temperature	-55 to 150 °C

DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

Symbol

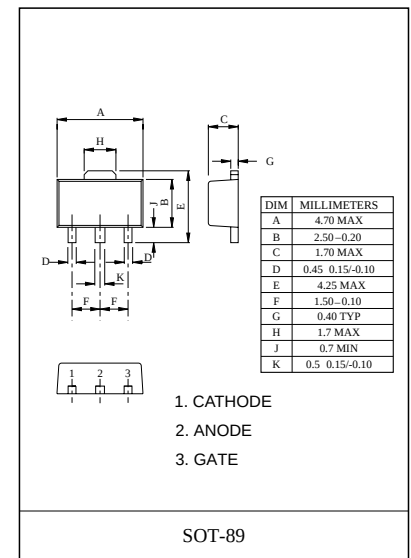


FEATURES

- Blocking voltage to 400 V (MCR100-6/F) , 600V (MCR100-8/F)
- RMS on-state current to 0.8 A
- General purpose switching

APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays.



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCR100-6/F MCR100-8/F	V_{DRM} AND V_{RRM}	$I_{DRM}= 10 \mu A$	400 600		V
Peak forward or reverse blocking current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7V$	5	25	μA
			15	30	μA
			20	100	μA
			80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

Typical Characteristics

